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AMENDMENT TRANSMITTAL LETTER						Docket No. M4065.0210/P210	
Applicatio		Filing I	- 1	Examiner		Art Unit	
09/588,008		June 6, 2000		Vikki H. Trin	h	2814	
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Attorney Reg. N DICKSTEIN SH		N & OSHINSK	VIID				
2101 L Street N		V & OSI IIIVSK	I LLP				
Washington, DO							
(202) 828-2232							



Docket No.: M4065.0210/P210

(PATENT)

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Examiner: Vikki Trinh

Sam Yang, et al.

Application No.: 09/588,008

Art Unit: 2814

Filed: June 6, 2000

For: IMPROVED MEMORY CELL CAPACITOR

STRUCTURE AND METHOD OF

**FORMATION** 

## **AMENDMENT**

Commissioner for Patents MS: Amendment P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

This paper is in response to the Office Action dated March 11, 2004, please amend the above-identified U.S. patent application as follows:

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Remarks begin on page 8 of this paper.